

HIGH PERFORMANCE	50	60	70
Max. $\overline{\text{RAS}}$ Access Time, (t_{RAC})	50 ns	60 ns	70 ns
Max. Column Address Access Time, (t_{CAA})	25 ns	30 ns	35 ns
Min. Extended Data Out Page Mode Cycle Time, (t_{PC})	20 ns	25 ns	30 ns
Min. Read/Write Cycle Time, (t_{RC})	84 ns	104 ns	124 ns

Features

- 1M x 16-bit organization
- EDO Page Mode for a sustained data rate of 50 MHz
- $\overline{\text{RAS}}$ access time: 50, 60, 70 ns
- Dual $\overline{\text{CAS}}$ Inputs
- Low power dissipation
- Read-Modify-Write, $\overline{\text{RAS}}$ -Only Refresh, $\overline{\text{CAS}}$ -Before- $\overline{\text{RAS}}$ Refresh, Hidden Refresh, and Self Refresh.
- Refresh Interval: 1024 cycles/16 ms
- Available in 42-pin 400 mil SOJ and 50/44-pin 400 mil TSOP-II
- Single +3.3 V ± 0.3 V Power Supply
- TTL Interface

Description

The V53C318165A is a 1048576 x 16 bit high-performance CMOS dynamic random access memory. The V53C318165A offers Page mode operation with Extended Data Output. The V53C318165A has an symmetric address, 10-bit row and 10-bit column.

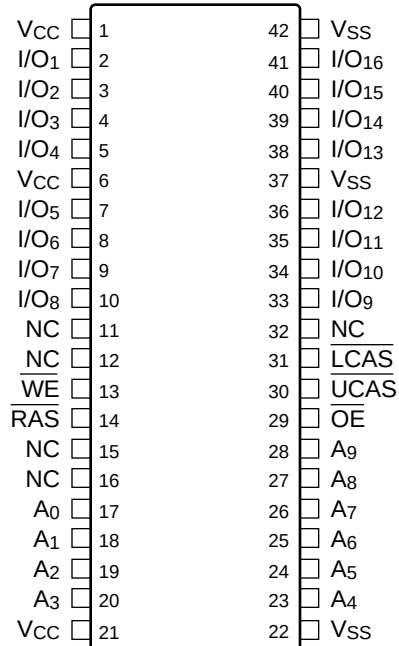
All inputs are TTL compatible. EDO Page Mode operation allows random access up to 1024 x 16 bits, within a page, with cycle times as short as 20ns.

These features make the V53C318165A ideally suited for a wide variety of high performance computer systems and peripheral applications.

Device Usage Chart

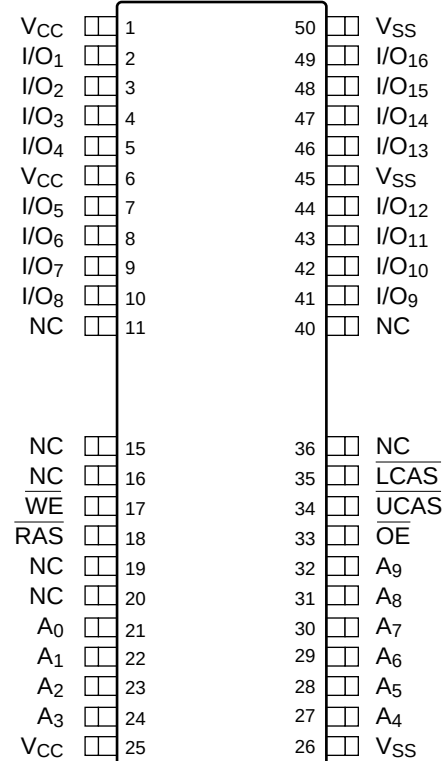
Operating Temperature Range	Package Outline		Access Time (ns)			Power	Temperature Mark
	K	T	50	60	70	Std.	
0°C to 70 °C	•	•	•	•	•	•	Blank

42-Pin Plastic SOJ
PIN CONFIGURATION
Top View



311816500-02

50/44-Pin Plastic TSOP-II
PIN CONFIGURATION
Top View



311816500-03

Pin Names

A ₀ –A ₉	Row, Column Address Inputs
$\overline{\text{RAS}}$	Row Address Strobe
$\overline{\text{UCAS}}$	Column Address Strobe/Upper Byte Control
$\overline{\text{LCAS}}$	Column Address Strobe/Lower Byte Control
$\overline{\text{WE}}$	Write Enable
$\overline{\text{OE}}$	Output Enable
I/O ₁ –I/O ₁₆	Data Input, Output
V _{CC}	+3.3V Supply
V _{SS}	0V Supply
NC	No Connect

Description	Pkg.	Pin Count
SOJ	K	42
TSOP-II	T	50

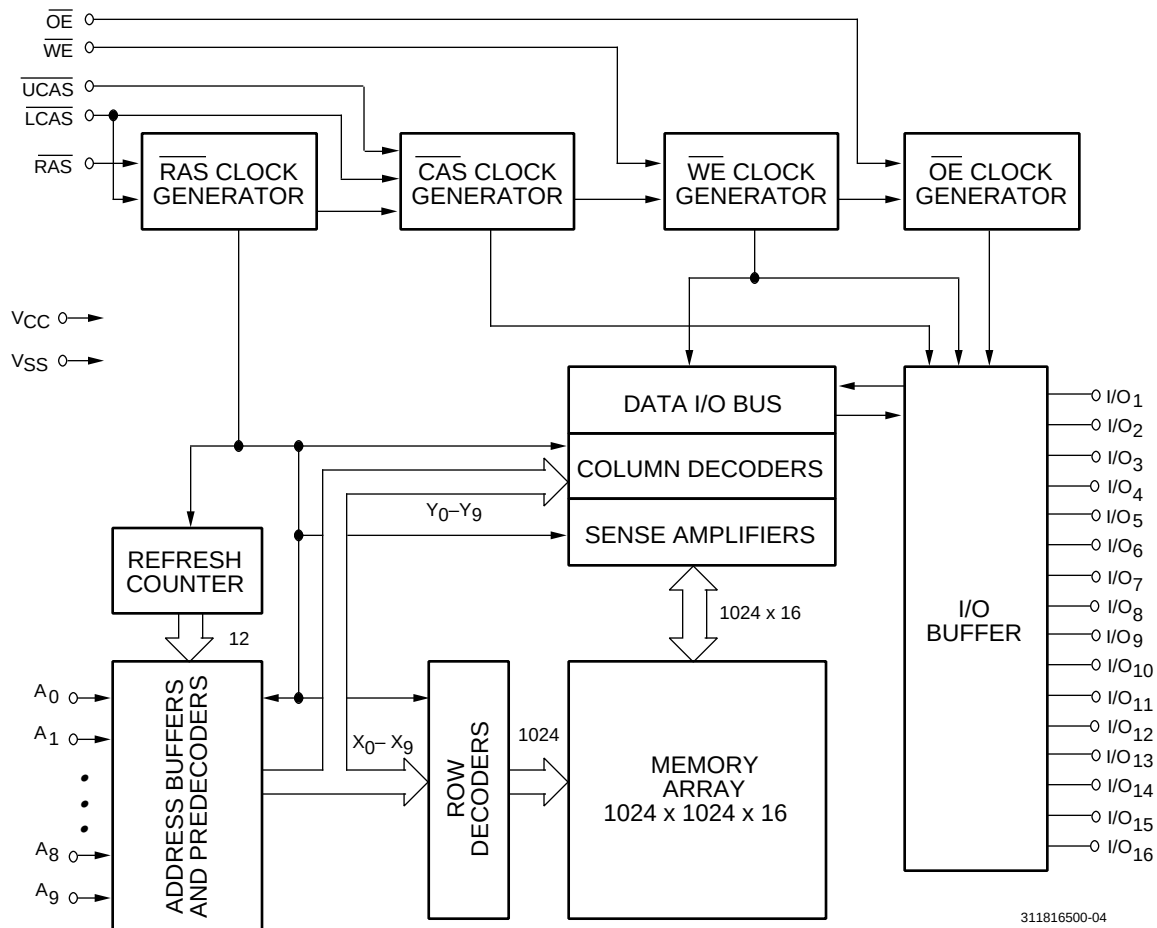
Capacitance*

$$T_A = 25^\circ\text{C}, V_{CC} = 3.3\text{ V} \pm 0.3\text{ V}, V_{SS} = 0\text{ V}, f = 1\text{ MHz}$$

Symbol	Parameter	Min.	Max.	Unit
C _{IN1}	Address Input	—	5	pF
C _{IN2}	RAS, UCAS, LCAS, WE, OE	—	7	pF
C _{OUT}	Data Input/Output	—	7	pF

***Note:** Capacitance is sampled and not 100% tested.

1024 x 16



DC and Operating Characteristics (1-2)

$T_A = 0^{\circ}\text{C}$ to 70°C , $V_{CC} = 3.3\text{ V} \pm 0.3\text{ V}$, $V_{SS} = 0\text{ V}$, $t_T = 2\text{ ns}$, unless otherwise specified.

Symbol	Parameter	Access Time	V53C318165A			Unit	Test Conditions	Notes
			Min.	Typ.	Max.			
I_{LI}	Input Leakage Current (any input pin)		-10		10	μA	$V_{SS} \leq V_{IN} \leq V_{CC} + 0.3\text{V}$	1
I_{LO}	Output Leakage Current (for High-Z State)		-10		10	μA	$V_{SS} \leq V_{OUT} \leq V_{CC} + 0.3\text{V}$ RAS, CAS at V_{IH}	1
I_{CC1}	V_{CC} Supply Current, Operating	50			200	mA	$t_{RC} = t_{RC}(\text{min.})$	2, 3, 4
		60			180			
		70			160			
I_{CC2}	V_{CC} Supply Current, TTL Standby				2	mA	RAS, CAS at V_{IH} other inputs $\geq V_{SS}$	
I_{CC3}	V_{CC} Supply Current, RAS-Only Refresh	50			200	mA	$t_{RC} = t_{RC}(\text{min.})$	2, 4
		60			180			
		70			160			
I_{CC4}	V_{CC} Supply Current, EDO Page Mode Operation	50			90	mA	Minimum Cycle	2, 3, 4
		60			75			
		70			60			
I_{CC5}	V_{CC} Supply Current, CMOS Standby				1.0	mA	RAS $\geq V_{CC} - 0.2\text{ V}$, CAS $\geq V_{CC} - 0.2\text{ V}$	1
I_{CC6}	Average Self Refresh Current CBR cycle with $t_{RAS} > t_{RASS} \text{ min.}$, (L-version only) CAS held low, $\overline{WE} = V_{CC} - 0.2\text{V}$, Address and $D_{IN} = V_{CC} - 0.2\text{V}$ or 0.2V				1.0	mA		
I_{CC7}	V_{CC} Supply Current, during CAS-before-RAS Refresh	50			200	mA	$t_{RC} = t_{RC}(\text{min})$	2, 4
		60			180			
		70			160			
V_{IL}	Input Low Voltage		-0.5		0.8	V		1
V_{IH}	Input High Voltage		2		$V_{CC} + 0.5$	V		1
V_{OL}	Output Low Voltage				0.4	V	$I_{OL} = 2\text{ mA}$	1
V_{OH}	Output High Voltage		2.4			V	$I_{OH} = -2\text{ mA}$	1

AC Characteristics

$T_A = 0^\circ\text{C}$ to 70°C , $V_{CC} = 3.3\text{ V} \pm 0.3\text{ V}$, $V_{SS} = 0\text{V}$, $t_r = 2\text{ns}$ unless otherwise noted

#	JEDEC Symbol	Symbol	Parameter	50		60		70		Unit	Notes
				Min.	Max.	Min.	Max.	Min.	Max.		
1	t_{RL1RH1}	t_{RAS}	$\overline{RAS}$ Pulse Width	50	10K	60	10K	70	10K	ns	
2	t_{RL2RL2}	t_{RC}	Read or Write Cycle Time	84		104		124		ns	
3	t_{RH2RL2}	t_{RP}	$\overline{RAS}$ Precharge Time	30		40		50		ns	
4	t_{RL1CH1}	t_{CSH}	$\overline{CAS}$ Hold Time	40		50		60		ns	
5	t_{CL1CH1}	t_{CAS}	$\overline{CAS}$ Pulse Width	8	10K	10	10K	12	10K	ns	
6	t_{RL1CL1}	t_{RCD}	$\overline{RAS}$ to $\overline{CAS}$ Delay	12	37	14	45	14	53	ns	
7	t_{WH2CL2}	t_{RCS}	Read Command Setup Time	0		0		0		ns	
8	t_{AVRL2}	t_{ASR}	Row Address Setup Time	0		0		0		ns	
9	t_{RL1AX}	t_{RAH}	Row Address Hold Time	8		10		10		ns	
10	t_{AVCL2}	t_{ASC}	Column Address Setup Time	0		0		0		ns	
11	t_{CL1AX}	t_{CAH}	Column Address Hold Time	8		10		12		ns	
12	$t_{CL1RH1(R)}$	t_{RSH}	$\overline{RAS}$ Hold Time	13		15		17		ns	
13	t_{CH2RL2}	t_{CRP}	$\overline{CAS}$ to $\overline{RAS}$ Precharge Time	5		5		5		ns	
14	t_{CH2WX}	t_{RCH}	Read Command Hold Time Referenced to $\overline{CAS}$	0		0		0		ns	9
15	t_{RH2WX}	t_{RRH}	Read Command Hold Time Referenced to $\overline{RAS}$	0		0		0		ns	9
16	t_{CL1}	t_{COH}	Output Hold after $\overline{CAS}$ LOW	5		5		5		ns	
17	t_{GL1QV}	t_{OAC}	Access Time from $\overline{OE}$		13		15		17	ns	
18	t_{CL1QV}	t_{CAC}	Access Time from $\overline{CAS}$		13		15		17	ns	7, 12
19	t_{RL1QV}	t_{RAC}	Access Time from $\overline{RAS}$		50		60		70	ns	7, 12
20	t_{AVQV}	t_{CAA}	Access Time from Column Address		25		30		35	ns	7, 13
21	t_{CL1QX}	t_{CLZ}	$\overline{CAS}$ to Low-Z Output	0		0		0		ns	7
22	t_{CH2QX}	t_{OFF}	Output Buffer Turnoff Delay	0	13	0	15	0	17	ns	
23	t_{CL1QZ}	t_{DZC}	Data to $\overline{CAS}$ Low Delay	0		0		0		ns	15
24	t_{RL1AV}	t_{RAD}	$\overline{RAS}$ to Column Address Delay Time	10	25	12	30	12	35	ns	
25	t_{GL2QZ}	t_{OEZ}	Output Buffer Turnoff Delay from $\overline{OE}$	0	13	0	15	0	17	ns	8
26	t_{WL1CH1}	t_{CWL}	Write Command to $\overline{CAS}$ Lead Time	13		15		17		ns	
27	t_{WL1CL2}	t_{WCS}	Write Command Setup Time	0		0		0		ns	11
28	t_{CL1WH1}	t_{WCH}	Write Command Hold Time	8		10		10		ns	
29	t_{WL1WH1}	t_{WP}	Write Pulse Width	8		10		10		ns	
30	t_{GL1QZ}	t_{DEO}	Data to $\overline{OE}$ Delay	0		0		0		ns	15
31	t_{WL1RH1}	t_{RWL}	Write Command to $\overline{RAS}$ Lead Time	13		15		17		ns	
32	t_{DVWL2}	t_{DS}	Data in Setup Time	0		0		0		ns	10

AC Characteristics (Cont'd)

#	JEDEC Symbol	Symbol	Parameter	50		60		70		Unit	Notes
				Min.	Max.	Min.	Max.	Min.	Max.		
33	t _{WL1DX}	t _{DH}	Data in Hold Time	8		10		12		ns	10
34	t _{WL1GL2}	t _{WOH}	Write to $\overline{OE}$ Hold Time	10		13		15		ns	10
35	t _{CH2RH2}	t _{PRWC}	EDO Page Mode Read-Write Cycle Time	58		68		77		ns	
36	t _{RL2RL2 (RMW)}	t _{RWC}	Read-Modify-Write Cycle Time	113		138		162		ns	
38	t _{CL1WL2}	t _{CWD}	$\overline{CAS}$ to $\overline{WE}$ Delay	27		32		36		ns	10
39	t _{RL1WL2}	t _{RWD}	$\overline{RAS}$ to $\overline{WE}$ Delay in Read-Modify-Write Cycle	64		77		89		ns	10
40	t _{AVWL2}	t _{AWD}	Column Address to $\overline{WE}$ Delay	39		47		54		ns	10
41	t _{CL2CL2}	t _{PC}	EDO Page Mode Read or Write Cycle Time	20		25		30		ns	
42	t _{CH2CL2}	t _{CP}	$\overline{CAS}$ Precharge Time	8		10		10		ns	
43	t _{AVRH1}	t _{CAR}	Column Address to $\overline{RAS}$ Setup Time	25		30		35		ns	
44	t _{CH2QV}	t _{CAP}	Access Time from Column Precharge		27		32		37	ns	6
46	t _{CL1RL2}	t _{CSR}	$\overline{CAS}$ Setup Time $\overline{CAS}$ -before- $\overline{RAS}$ Refresh	10		10		10		ns	
47	t _{RH2CL2}	t _{RPC}	$\overline{RAS}$ to $\overline{CAS}$ Precharge Time	5		5		5		ns	
48	t _{RL1CH1}	t _{CHR}	$\overline{CAS}$ Hold Time $\overline{CAS}$ -before- $\overline{RAS}$ Refresh	10		10		10		ns	
50	t _{RH2CL2}	t _{RASP}	$\overline{RAS}$ Pulse Width (EDO Mode)	50	200K	60	200K	70	200K	ns	
51	t _{RH2CL2}	t _{RHCP}	$\overline{CAS}$ Precharge Time to $\overline{RAS}$ Delay	27		32		37		ns	
52	t _{RH2CL2}	t _{CPWD}	$\overline{CAS}$ Precharge Time to $\overline{WE}$	41		49		56		ns	
53	t _{RH2CL2}	t _{CPT}	$\overline{CAS}$ Precharge Time (CBR Counter Test)	35		40		40		ns	
54	t _{RH2CL2}	t _{WRP}	Write to $\overline{RAS}$ Precharge time (CRB Cycle)	10		10		10		ns	
55	t _{RH2CL2}	t _{WRH}	Write Hold time reference to $\overline{RAS}$ (CRB Cycle)	10		10		10		ns	
56	t _{RH2CL2}	t _{CDD}	$\overline{CAS}$ High to Data delay	10		13		15		ns	16
57	t _{RH2CL2}	t _{ODD}	$\overline{OE}$ High to Data delay	10		13		15		ns	16
58	t _T	t _T	Transition Time (Rise and Fall)	1	50	1	50	1	50	ns	
59		t _{REF}	Refresh Interval (1024 Cycles)		16		16		16	ms	

Self Refresh AC Characteristics

60		t _{RASS}	$\overline{RAS}$ Pulse Width During Self Refresh	100K		100K		100K		ns	17
61		t _{RPS}	$\overline{RAS}$ Precharge Time During Self Refresh	95		110		130		ns	17
62		t _{CHS}	$\overline{CAS}$ Hold Time Width During Self Refresh	50		50		50		ns	17

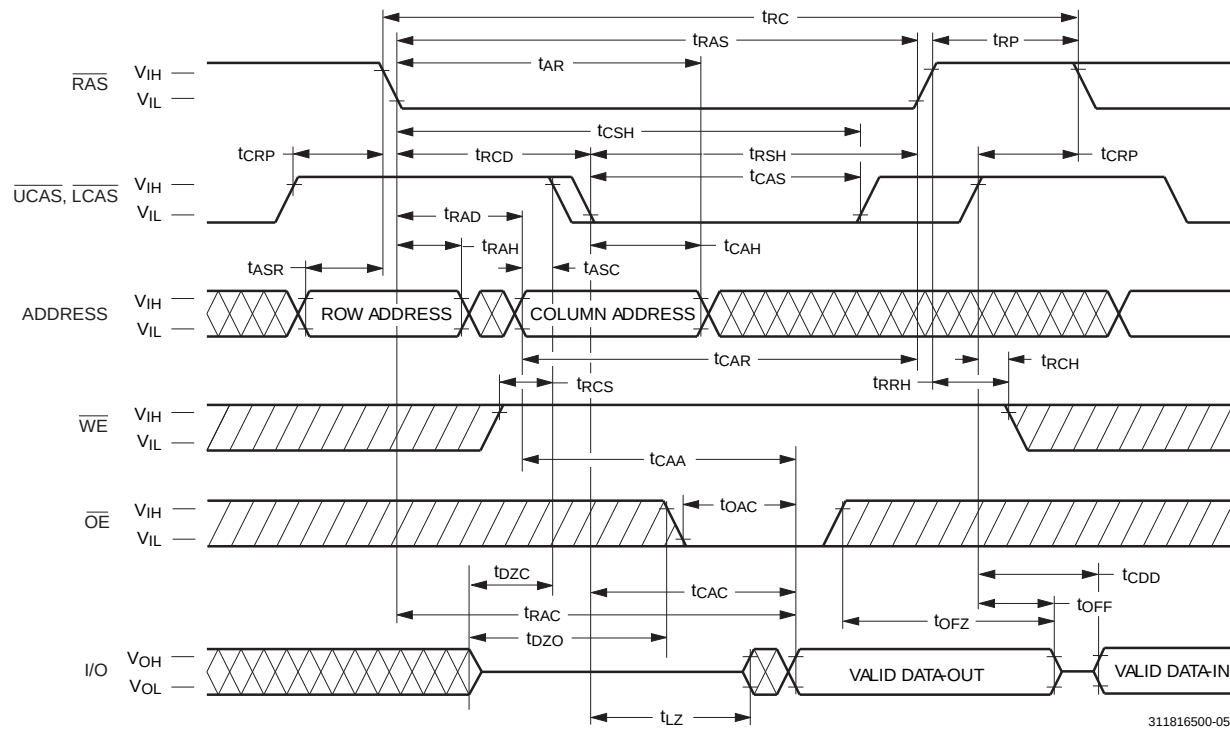
Notes:

1. All voltage are referenced to V_{SS} .
2. I_{CC1} , I_{CC3} , I_{CC4} , and I_{CC7} depend on cycle rate.
3. I_{CC1} and I_{CC4} depend on output loading. Specified values are measured with the output open.
4. Address can be changed once or less while $\overline{RAS} = V_{IL}$. In the case of I_{CC4} it can be changed once or less during an EDO cycle (t_{HPC}).
5. An initial pause of 200 μs is required after power-up followed by 8 $\overline{RAS}$ cycles of which at least one cycle has to be a refresh cycle, before proper device operation is achieved. In case of using internal refresh counter, a minimum of 8 $\overline{CAS}$ -before- $\overline{RAS}$ initialization cycles instead of 8 $\overline{RAS}$ cycles are required.
6. V_{IH} (min.) and V_{IL} (max.) are reference levels for measuring timing of input signals. Transition times are also measured between V_{IH} and V_{IL} .
7. Measured with a load equivalent to 2 TTL gates and 50 pF ($V_{OL} = 0.8V$ and $V_{OH} = 2.0V$).
8. t_{OFF} (max.) and t_{OEZ} (max.) define the time at which the outputs achieve the open-circuit condition and are not referenced to output voltage levels.
9. Either t_{RCH} or t_{RRH} must be satisfied for a read cycle.
10. These parameters are referenced to the $\overline{CAS}$ leading edge in early write cycles and to the $\overline{WE}$ leading edge in read-write cycles.
11. t_{WCS} , t_{RWD} , t_{CWD} , t_{AWD} and t_{CPWD} are not restrictive operating parameters. They are included in the data sheet as electrical characteristics only. If $t_{WCS} > t_{WCS}(\text{min.})$, the cycle is an early write cycle and the I/O pin will remain open-circuit (high impedance) through the entire cycle; if $t_{RWD} > t_{RWD}(\text{min.})$, $t_{CWD} > t_{CWD}(\text{min.})$, $t_{AWD} > t_{AWD}(\text{min.})$, and $t_{CPWD} > t_{CPWD}(\text{min.})$, the cycle is a read-write cycle and I/O pins will contain data read from the selected cells. If neither of the above sets of conditions is satisfied, the condition of the I/O pins (at access time) is indeterminate.
12. Operation within the $t_{RCD}(\text{max.})$ limit ensures that $t_{RAC}(\text{max.})$ can be met. $t_{RCD}(\text{max.})$ is specified as a reference point only: if t_{RCD} is greater than the specified $t_{RCD}(\text{max.})$ limit, then access time is controlled by t_{CAC} .
13. Operation within the $t_{RAD}(\text{max.})$ limit ensures that $t_{RAC}(\text{max.})$ can be met. $t_{RAD}(\text{max.})$ is specified as a reference point only: if t_{RAD} is greater than the specified $t_{RAD}(\text{max.})$ limit, then access time is controlled by t_{CAA} .
14. AC measurements assume $t_f = 2 \text{ ns}$.
15. Either t_{DZC} or t_{DEO} must be satisfied.
16. Either t_{CDD} or t_{ODD} must be satisfied.
17. When using Self Refresh mode, the following refresh operations must be performed to ensure proper DRAM operation:

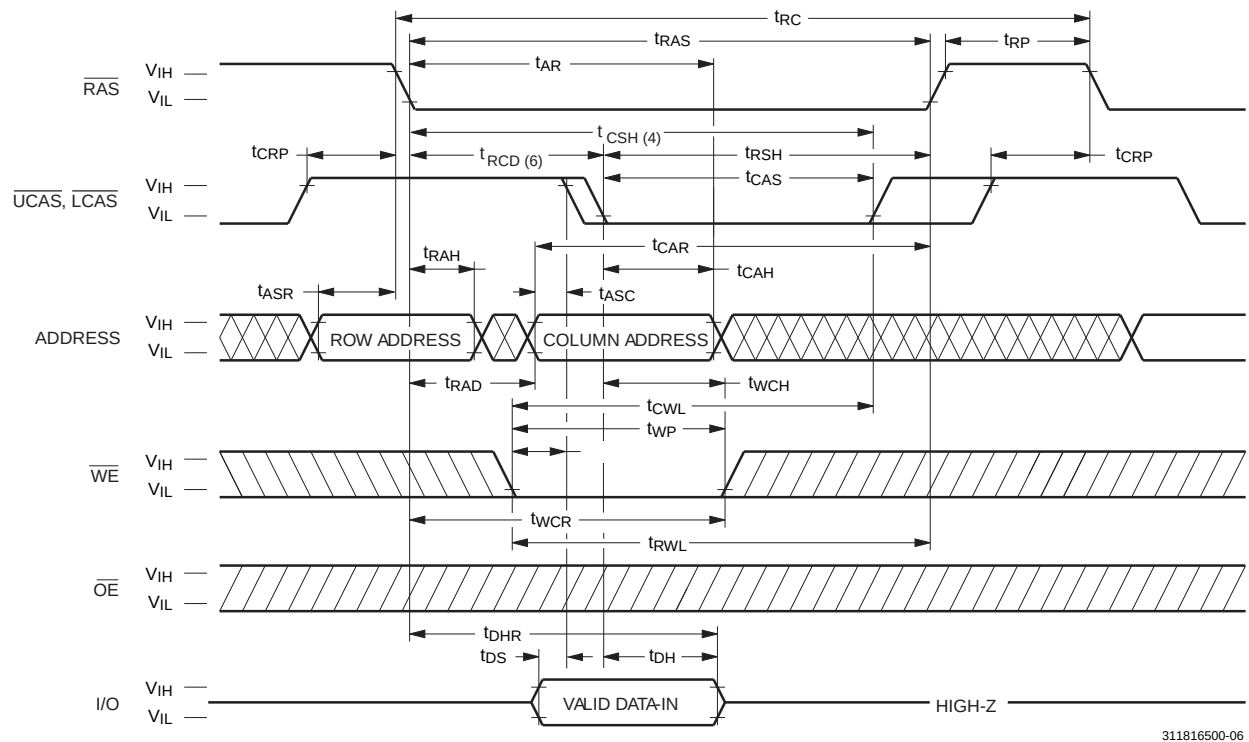
If row addresses are being refreshed on an evenly distributed manner over the refresh interval using CBR refresh cycles, then only one CBR cycle must be performed immediately after exit from Self Refresh.

If row addresses are being refreshed in any other manner (ROR – Distributed/Burst; or CBR – Burst) over the refresh interval, then a full set of row refreshes must be performed immediately before entry to and immediately after exit from Self Refresh.
18. t_{OFF} is referenced from the rising edge of $\overline{RAS}$ or $\overline{CAS}$, whichever occurs last.

Waveforms of Read Cycle



Waveforms of Early Write Cycle



Don't Care

Undefined

The timing diagram illustrates the relationship between several control and data signals for the 311816500-0 device. The signals shown are:

- RAS**: Row Address Strobe, active low. Timing parameters include t_{AR} (access time), t_{RAS} (RAS to CAS delay), t_{RC} (RAS to column address delay), t_{RP} (RAS pulse width), and t_{CRP} (RAS to column address delay).
- UCAS, LCAS**: Column Address Strobe and Local Column Address Strobe, active low. Timing parameters include t_{CRP} (column address pulse width), t_{RCD} (RAS to column address delay), t_{CSH} (column address setup time), t_{RSH} (RAS to column address delay), t_{CAS} (column address setup time), t_{RAD} (RAS to data delay), t_{CAR} (column address to row address delay), and t_{CAH} (column address hold time).
- ADDRESS**: Row and Column Address. The diagram shows the timing for ROW ADDRESS and COLUMN ADDRESS, with parameters t_{ASR} (address setup time), t_{RAH} (row address hold time), t_{ASC} (address to column address delay), and t_{CAH} (column address hold time).
- WE**: Write Enable, active low. Timing parameters include t_{CWL} (write enable to column address delay), t_{RWL} (write enable to row address delay), and t_{WP} (write enable pulse width).
- OE**: Output Enable, active low. Timing parameters include t_{WOH} (output enable to column address delay), t_{OED} (output enable delay), and t_{DS} (output delay).
- I/O**: Data Input/Output. The diagram shows the timing for VALID DATA-IN, with parameters t_{DH} (data hold time) and t_{DS} (data setup time).

The timing diagram illustrates the relationship between several control and data signals for the 311816500-0 device. The signals and their timing parameters are as follows:

- RAS:** Row Address Strobe. Timing parameters include t_{AR} (access time), t_{RAS} (row address strobe pulse width), t_{RWC} (row-to-column delay), and t_{RP} (row precharge time).
- UCAS, LCAS:** Column Address Strobe/Latch Enable. Timing parameters include t_{CRP} (column precharge time), t_{RCD} (row-to-column delay), t_{CSH} (column strobe hold time), t_{RSH} (row-to-column delay), t_{CAS} (column address strobe pulse width), and t_{CRP} (column precharge time).
- ADDRESS:** Data Address. Timing parameters include t_{ASR} (address strobe rise time), t_{RAH} (row address hold time), t_{ASC} (address strobe fall time), t_{CAH} (column address hold time), t_{RAD} (row address delay), t_{AWD} (address-to-data delay), t_{CWD} (column address-to-data delay), t_{RWD} (row address-to-data delay), t_{CWL} (column address-to-data delay), t_{RWL} (row address-to-data delay), and t_{WP} (write pulse width).
- WE:** Write Enable. Timing parameters include t_{DZO} (data-to-write enable delay), t_{CAA} (column address-to-write enable delay), and t_{OAC} (output-to-address delay).
- OE:** Output Enable. Timing parameters include t_{DZC} (data-to-output enable delay), t_{CAC} (column address-to-output enable delay), t_{OED} (output-to-data delay), t_{OEZ} (output-to-zero delay), t_{DS} (data-to-strobe delay), and t_{DH} (data-to-hold delay).
- I/O:** Data Input/Output. Timing parameters include t_{RAC} (row address-to-output delay), t_{LZ} (load time), t_{OH} (output high time), and t_{OL} (output low time).

[illegible]

The diagram illustrates the timing relationships for the 311816500-1 device. It shows the following signals and their timing parameters:

- RAS:** $\overline{\text{RAS}}$ signal with parameters t_{AR} , t_{RASP} , and t_{RP} .
- UCAS, LCAS:** $\overline{\text{UCAS}}$, $\overline{\text{LCAS}}$ signals with parameters t_{CRP} , t_{PC} , t_{CP} , t_{CAS} , t_{RSH} , and t_{CRP} .
- ADDRESS:** ADDRESS signal with parameters t_{RAH} , t_{CAH} , t_{CWL} , t_{WCS} , t_{WCH} , t_{WP} , and t_{RAD} . The signal is divided into ROW ADDRESS and COLUMN ADDRESS segments.
- WE:** $\overline{\text{WE}}$ signal with parameters t_{WCS} , t_{WCH} , and t_{WP} .
- OE:** $\overline{\text{OE}}$ signal with parameters t_{WCS} , t_{WCH} , and t_{WP} .
- I/O:** I/O signal with parameters t_{DS} and t_{DH} . The signal is divided into VALID DATA IN and OPEN segments.

The diagram shows the timing relationships between these signals, including setup and hold times, and the duration of valid data in the I/O buffer.

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The timing diagram illustrates the relationship between several control and data signals over time. The signals and their associated timing parameters are as follows:

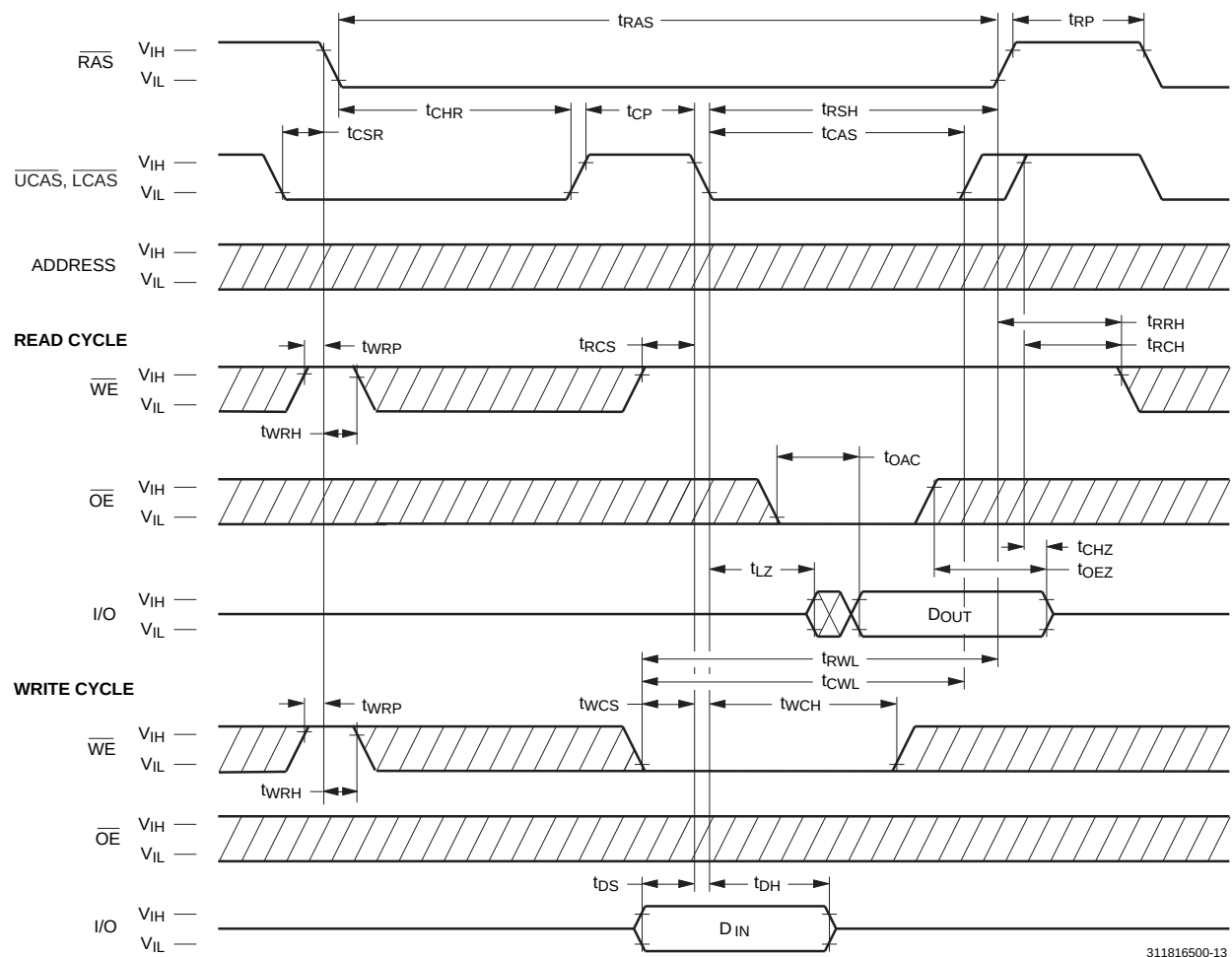
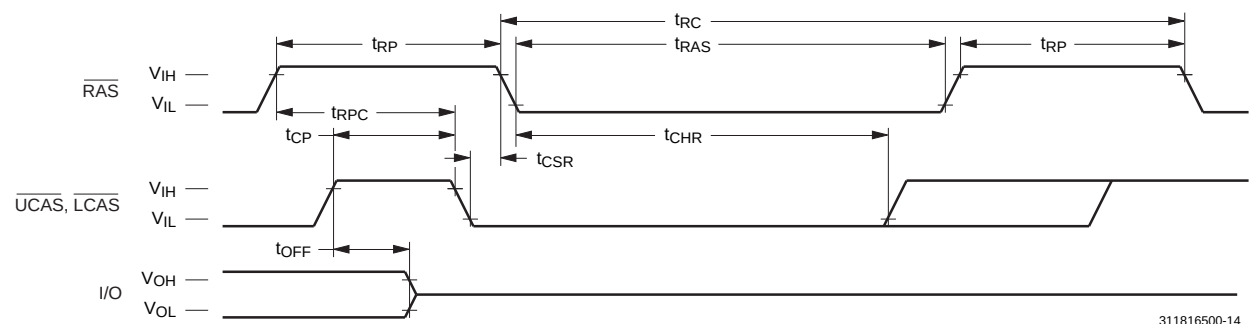
- RAS:** Shows a high-to-low transition followed by a low-to-high transition. Key parameters include t_{RSP} (RAS setup time), t_{RCD} (RAS-to-CAS delay), t_{RSH} (RAS-to-high delay), and t_{RCP} (RAS-to-column address delay).
- UCAS, LCAS:** Shows a high-to-low transition followed by a low-to-high transition. Key parameters include t_{RAD} (UCAS/LCAS-to-address delay), t_{RAH} (UCAS/LCAS-to-high delay), t_{CAS} (CAS setup/hold time), and t_{CRP} (UCAS/LCAS-to-column address delay).
- ADDRESS:** Shows a sequence of row and column addresses. Key parameters include t_{ASR} (address-to-strobe delay), t_{ASC} (address-to-strobe delay), t_{CAH} (column address-to-high delay), t_{CWD} (column address-to-data delay), and t_{CWL} (column address-to-low delay).
- WE (Write Enable):** Shows a high-to-low transition followed by a low-to-high transition. Key parameters include t_{WWD} (write enable-to-data delay), t_{WPL} (write enable-to-low delay), t_{WPD} (write enable-to-data delay), and t_{WPL} (write enable-to-low delay).
- OE (Output Enable):** Shows a high-to-low transition followed by a low-to-high transition. Key parameters include t_{OAC} (output enable-to-address delay), t_{OAZ} (output enable-to-address delay), t_{ODD} (output enable-to-data delay), and t_{ODD} (output enable-to-data delay).
- I/O:** Shows a sequence of output and input data. Key parameters include t_{LZ} (load-to-zero delay), t_{PS} (pull-up/pull-down delay), and t_{PS} (pull-up/pull-down delay).

The diagram illustrates the timing relationships for the 311816500-12 device. It shows the following signals and their timing parameters:

- RAS:** The RAS signal transitions from V_{IH} to V_{IL} . The total duration of the low pulse is t_{RC} . The time from the falling edge of RAS to the start of the data output is t_{RAS} . The time from the rising edge of RAS to the end of the data output is t_{RP} . The time from the rising edge of RAS to the start of the data output is t_{CRP} .
- UCAS, LCAS:** The UCAS and LCAS signals transition from V_{IH} to V_{IL} . The time from the falling edge of UCAS/LCAS to the start of the data output is t_{ASR} .
- ADDRESS:** The ADDRESS signal transitions from V_{IH} to V_{IL} . The time from the falling edge of ADDRESS to the start of the data output is t_{RAH} .
- I/O:** The I/O signal transitions from V_{OH} to V_{OL} . The time from the falling edge of I/O to the start of the data output is t_{RAH} .

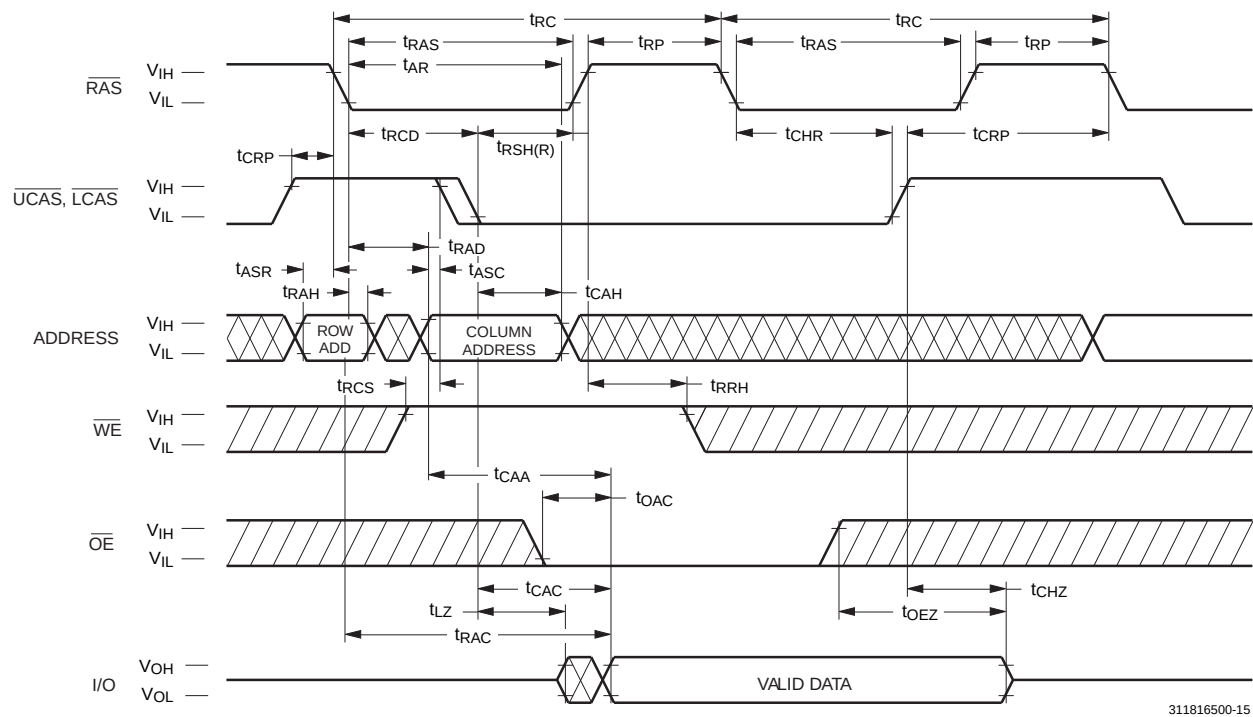
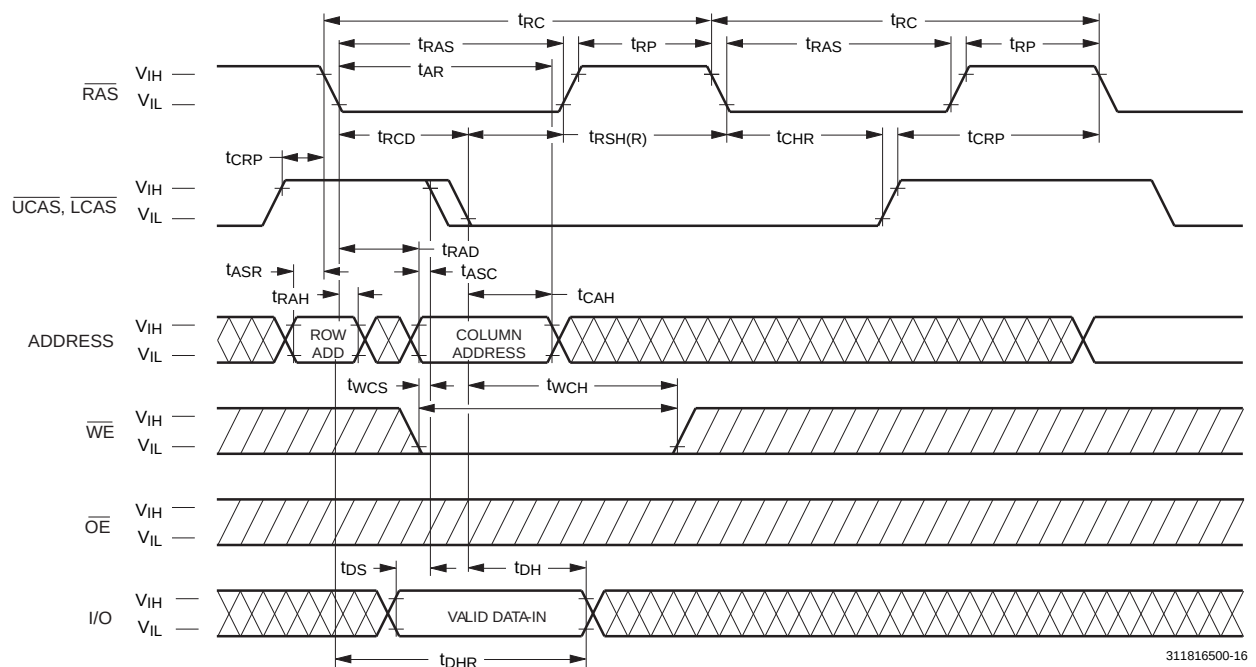
NOTE: $\overline{WE}$, $\overline{OE}$ = Don't care

311816500-12

Waveforms of $\overline{\text{CAS}}$ -before- $\overline{\text{RAS}}$ Refresh Counter Test Cycle**Waveforms of $\overline{\text{CAS}}$ -before- $\overline{\text{RAS}}$ Refresh Cycle**NOTE: $\overline{\text{WE}}$, $\overline{\text{OE}}$, A_0 - A_9 = Don't care

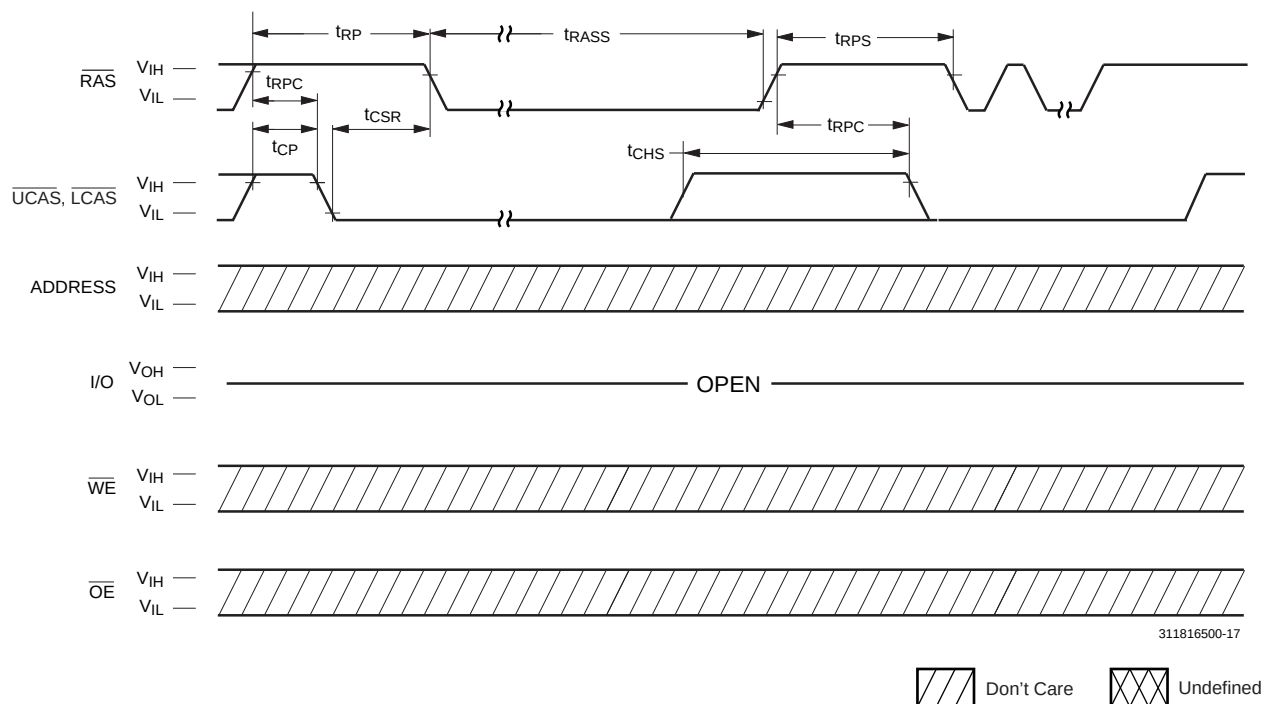
Don't Care

Undefined

Waveforms of Hidden Refresh Cycle (Read)**Waveforms of Hidden Refresh Cycle (Write)**

Don't Care

Undefined

Waveforms of Self Refresh Cycle (optional)**Functional Description**

The V53C318165A is a CMOS dynamic RAM optimized for high data bandwidth, low power applications. It is functionally similar to a traditional dynamic RAM. The V53C318165A reads and writes data by multiplexing an 20-bit address into a 10-bit row and a 10-bit column address. The row address is latched by the Row Address Strobe ($\overline{\text{RAS}}$). The column address “flows through” an internal address buffer and is latched by the Column Address Strobe ($\overline{\text{CAS}}$). Because access time is primarily dependent on a valid column address rather than the precise time that the $\overline{\text{CAS}}$ edge occurs, the delay time from $\overline{\text{RAS}}$ to $\overline{\text{CAS}}$ has little effect on the access time.

Memory Cycle

A memory cycle is initiated by bringing $\overline{\text{RAS}}$ low. Any memory cycle, once initiated, must not be ended or aborted before the minimum t_{RAS} time has expired. This ensures proper device operation and data integrity. A new cycle must not be initiated until the minimum precharge time $t_{\text{RP}}/t_{\text{CP}}$ has elapsed.

Read Cycle

A Read cycle is performed by holding the Write Enable ($\overline{\text{WE}}$) signal High during a $\overline{\text{RAS}}$ / $\overline{\text{CAS}}$ operation. The column address must be held for a minimum specified by t_{AR} . Data Out becomes valid only when t_{OAC} , t_{RAC} , t_{CAA} and t_{CAC} are all satisfied. As a result, the access time is dependent on the timing relationships between these parameters. For example, the access time is limited by t_{CAA} when t_{RAC} , t_{CAC} and t_{OAC} are all satisfied.

Write Cycle

A Write Cycle is performed by taking $\overline{\text{WE}}$ and $\overline{\text{CAS}}$ low during a $\overline{\text{RAS}}$ operation. The column address is latched by $\overline{\text{CAS}}$. The Write Cycle can be $\overline{\text{WE}}$ controlled or $\overline{\text{CAS}}$ controlled depending on whether $\overline{\text{WE}}$ or $\overline{\text{CAS}}$ falls later. Consequently, the input data must be valid at or before the falling edge of $\overline{\text{WE}}$ or $\overline{\text{CAS}}$, whichever occurs last. In the $\overline{\text{CAS}}$ -controlled Write Cycle, when the leading edge of $\overline{\text{WE}}$ occurs prior to the $\overline{\text{CAS}}$ low transition, the I/O data pins will be in the High-Z state at the beginning of the Write function. Ending the Write with $\overline{\text{RAS}}$ or $\overline{\text{CAS}}$ will maintain the output in the High-Z state.

In the $\overline{\text{WE}}$ controlled Write Cycle, $\overline{\text{OE}}$ must be in the high state and t_{OED} must be satisfied.

Extended Data Output Page Mode

EDO Page operation permits all 1024 columns within a selected row of the device to be randomly accessed at a high data rate. Maintaining RAS low while performing successive CAS cycles retains the row address internally and eliminates the need to reapply it for each cycle. The column address buffer acts as a transparent or flow-through latch while CAS is high. Thus, access begins from the occurrence of a valid column address rather than from the falling edge of CAS, eliminating t_{ASC} and t_T from the critical timing path. CAS latches the address into the column address buffer. During EDO operation, Read, Write, Read-Modify-Write or Read-Write-Read cycles are possible at random addresses within a row. Following the initial entry cycle into EDO Mode, access is t_{CAA} or t_{CAP} controlled. If the column address is valid prior to the rising edge of CAS, the access time is referenced to the CAS rising edge and is specified by t_{CAP} . If the column address is valid after the rising CAS edge, access is timed from the occurrence of a valid address and is specified by t_{CAA} . In both cases, the falling edge of CAS latches the address and enables the output.

EDO provides a sustained data rate of 50 MHz for applications that require high bandwidth such as bit-mapped graphics or high-speed signal processing. The following equation can be used to calculate the maximum data rate:

$$\text{Data Rate} = \frac{1024}{t_{RC} + 1023 \times t_{PC}}$$

Self Refresh

Self Refresh mode provides internal refresh control signals to the DRAM during extended periods of inactivity. Device operation in this mode provides additional power savings and design ease by elimination of external refresh control signals. Self Refresh mode is initiated with a CAS before RAS (CBR) Refresh cycle, holding both RAS low (t_{RASS}) and CAS low (t_{CHD}) for a specified period. Both of these parameters are specified with minimum values to guarantee entry into Self Refresh operation. Once the device has been placed in to Self Refresh mode the CAS clock is no longer required to maintain Self Refresh operation.

The Self Refresh mode is terminated by returning the RAS clock to a high level for a specified (t_{RPS}) minimum time. After termination of the Self Refresh cycle normal accesses to the device may be initiated immediately, providing that subsequent refresh cycles utilize the CAS before RAS (CBR) mode of operation.

Data Output Operation

The V53C318165A Input/Output is controlled by OE, CAS, WE and RAS. A RAS low transition enables the transfer of data to and from the selected row address in the Memory Array. A RAS high transition disables data transfer and latches the output data if the output is enabled. After a memory cycle is initiated with a RAS low transition, a CAS low transition or CAS low level enables the internal I/O path. A CAS high transition or a CAS high level disables the I/O path and the output driver if it is enabled. A CAS low transition while RAS is high has no effect on the I/O data path or on the output drivers. The output drivers, when otherwise enabled, can be disabled by holding OE high. The OE signal has no effect on any data stored in the output latches. A WE low level can also disable the output drivers when CAS is low. During a Write cycle, if WE goes low at a time in relationship to CAS that would normally cause the outputs to be active, it is necessary to use OE to disable the output drivers prior to the WE low transition to allow Data In Setup Time (t_{DS}) to be satisfied.

Power-On

After application of the V_{CC} supply, an initial pause of 200 μs is required followed by a minimum of 8 initialization cycles (any combination of cycles containing a RAS clock). Eight initialization cycles are required after extended periods of bias without clocks (greater than the Refresh Interval).

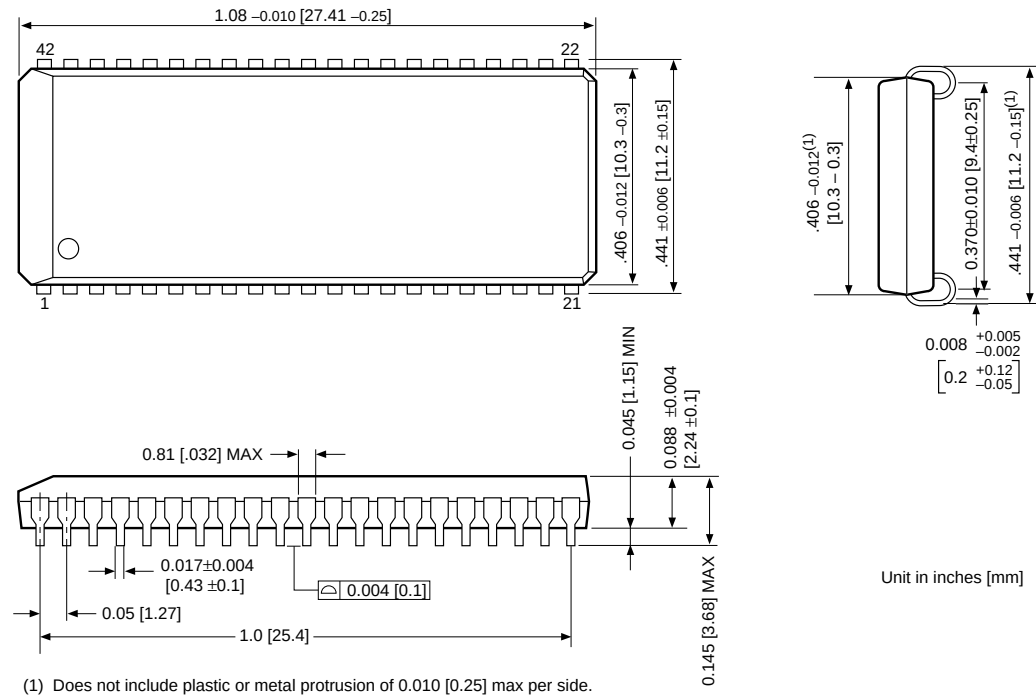
During Power-On, the V_{CC} current requirement of the V53C318165A is dependent on the input levels of RAS and CAS. If RAS is low during Power-On, the device will go into an active cycle and I_{CC} will exhibit current transients. It is recommended that RAS and CAS track with V_{CC} or be held at a valid V_{IH} during Power-On to avoid current surges.

Table 1. V53C318165A Data Output
Operation for Various Cycle Types

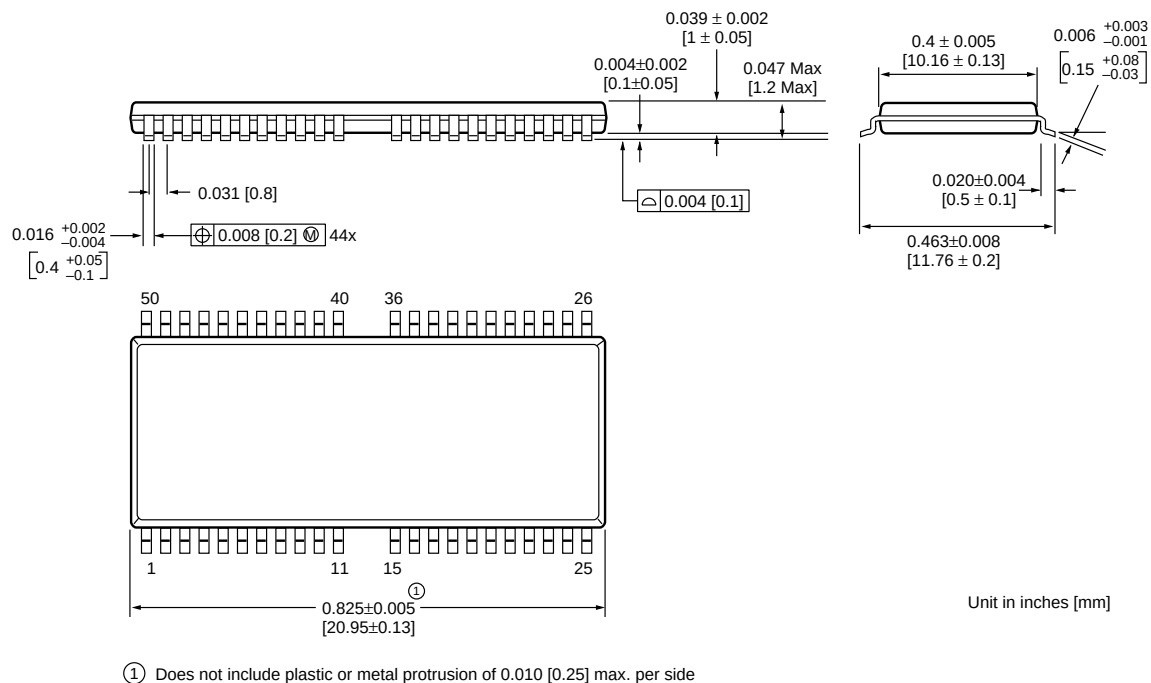
Cycle Type	I/O State
Read Cycles	Data from Addressed Memory Cell
CAS-Controlled Write Cycle (Early Write)	High-Z
$\overline{WE}$ -Controlled Write Cycle (Late Write)	$\overline{OE}$ Controlled. High $\overline{OE}$ = High-Z I/Os
Read-Modify-Write Cycles	Data from Addressed Memory Cell
EDO Read Cycle	Data from Addressed Memory Cell
EDO Write Cycle (Early Write)	High-Z
EDO Read-Modify-Write Cycle	Data from Addressed Memory Cell
$\overline{RAS}$ -only Refresh	High-Z
$\overline{CAS}$ -before- $\overline{RAS}$ Refresh Cycle	High-Z
$\overline{CAS}$ -only Cycles	High-Z

Package Diagrams

42-Pin 400 mil SOJ



50/44-Pin 400 mil TSOP-II



U.S.A.

3910 NORTH FIRST STREET
SAN JOSE, CA 95134
PHONE: 408-433-6000
FAX: 408-433-0185

HONG KONG

19 DAI FU STREET
TAIPO INDUSTRIAL ESTATE
TAIPO, NT, HONG KONG
PHONE: 011-852-665-4883
FAX: 011-852-664-7535

TAIWAN

7F, NO. 102
MIN-CHUAN E. ROAD, SEC. 3
TAIPEI
PHONE: 011-886-2-545-1213
FAX: 011-886-2-545-1209

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HSIN CHU, TAIWAN, R.O.C.
PHONE: 011-886-35-783344
FAX: 011-886-35-792838

JAPAN

WBG MARINE WEST 25F
6, NAKASE 2-CHOME
MIHAMA-KU, CHIBA-SHI
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FAX: 972-690-0341

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